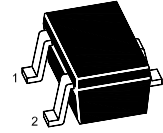


NPN Silicon Epitaxial Planar Transistor

for general purpose and switching applications



1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	BC846W 80	V
BC847W 50			
BC848W 30			
BC849W 30			
BC850W 50			
Collector Emitter Voltage	V_{CEO}	BC846W 65	V
BC847W 45			
BC848W 30			
BC849W 30			
BC850W 45			
Emitter Base Voltage	V_{EBO}	BC846W 6	V
BC847W 6			
BC848W 5			
BC849W 5			
BC850W 5			
Collector Current	I_C	100	mA
Peak Collector Current	I_{CM}	200	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

MARKING CODE

TYPE	846AW	846BW	846CW	847AW	847BW	847CW	848AW	848BW	848CW
MARKING	1A	1B	1C	1E	1F	1G	1J	1K	1L
TYPE	849AW	849BW	849CW	850AW	850BW	850CW			
MARKING	2A	2B	2C	2E	2F	2G			



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SOT-323



BC846W-BC850W

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Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$	BC846AW~BC850AW	h_{FE}	110	220	-
	BC846BW~BC850BW	h_{FE}	200	450	-
	BC846CW~BC850CW	h_{FE}	420	800	-
Collector Base Voltage at $I_C = 10\text{ }\mu\text{A}$	BC846W	V_{CBO}	80	-	V
	BC847W		50	-	
	BC848W		30	-	
	BC849W		30	-	
	BC850W		50	-	
Collector Emitter Voltage at $I_C = 10\text{ mA}$	BC846W	V_{CEO}	65	-	V
	BC847W		45	-	
	BC848W		30	-	
	BC849W		30	-	
	BC850W		45	-	
Emitter Base Voltage at $I_E = 1\text{ }\mu\text{A}$	BC846W	V_{EBO}	6	-	V
	BC847W		6	-	
	BC848W		5	-	
	BC849W		5	-	
	BC850W		5	-	
Collector Base Cutoff Current at $V_{CB} = 30\text{ V}$	I_{CBO}	-	15	nA	
Emitter Base Cutoff Current at $V_{EB} = 5\text{ V}$	I_{EBO}	-	100	nA	
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$	-	0.25	V	
		-	0.6		
Base Emitter Voltage at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$ $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$	V_{BE}	0.58	0.7	V	
		-	0.77		
Transition Frequency at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	-	MHz	
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$	C_{ob}	-	4.5	pF	

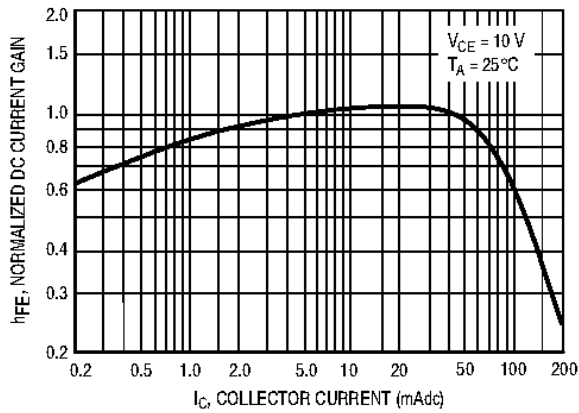


Figure 1. Normalized DC Current Gain

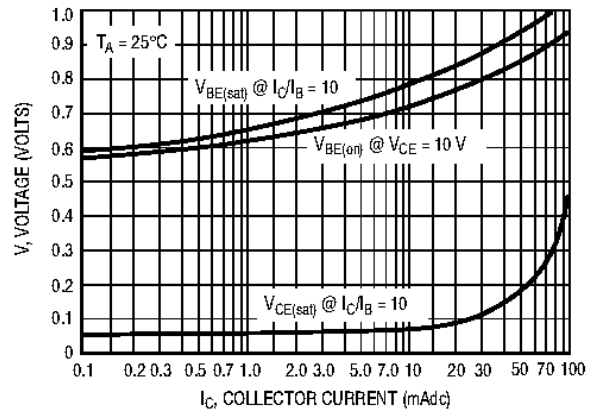


Figure 2. "Saturation" and "On" Voltages

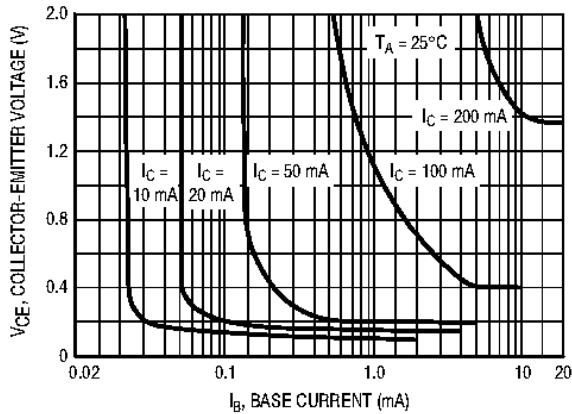


Figure 3. Collector Saturation Region

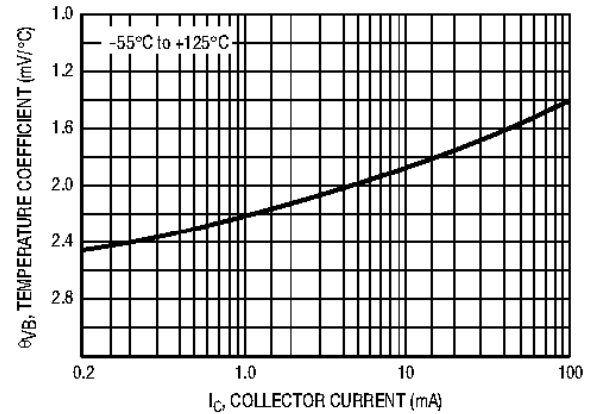


Figure 4. Base-Emitter Temperature Coefficient

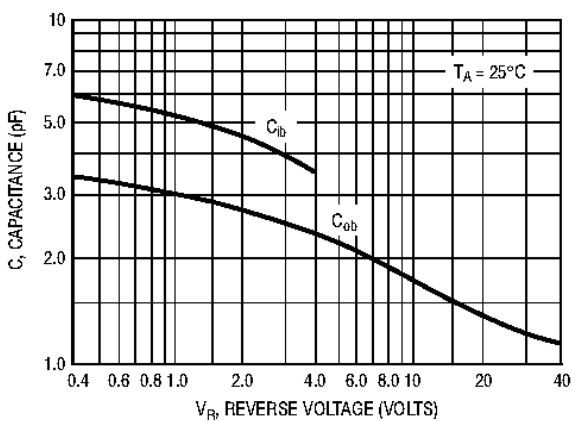


Figure 5. Capacitances

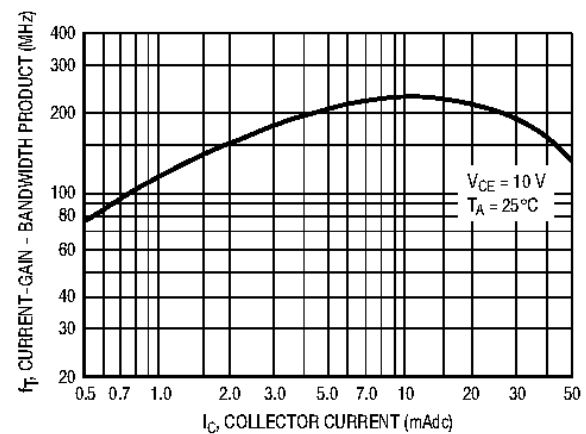


Figure 6. Current-Gain - Bandwidth Product



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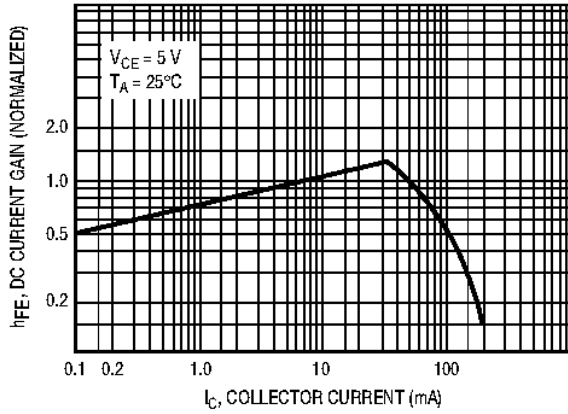


Figure 7. DC Current Gain

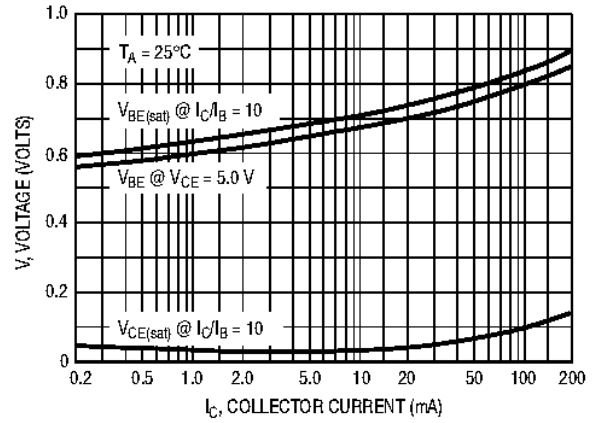


Figure 8. "On" Voltage

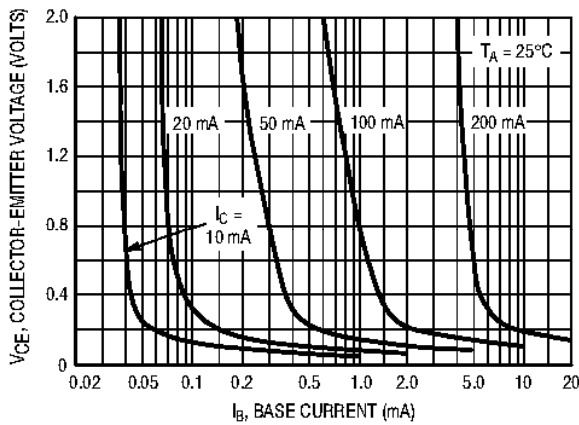


Figure 9. Collector Saturation Region

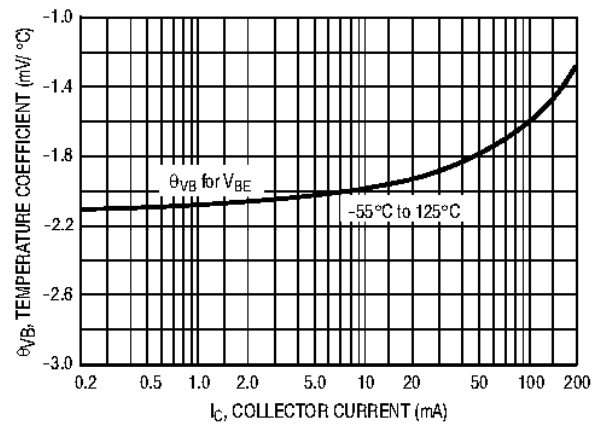


Figure 10. Base-Emitter Temperature Coefficient

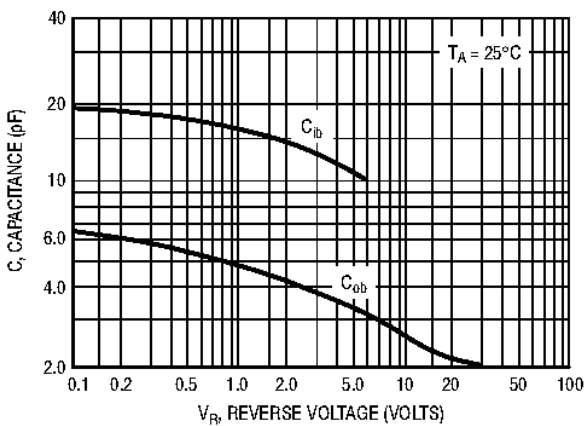


Figure 11. Capacitance

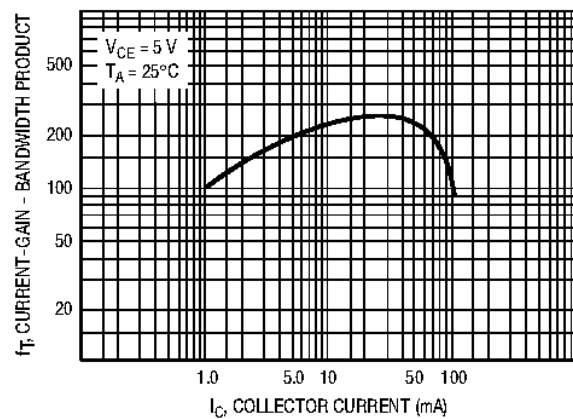
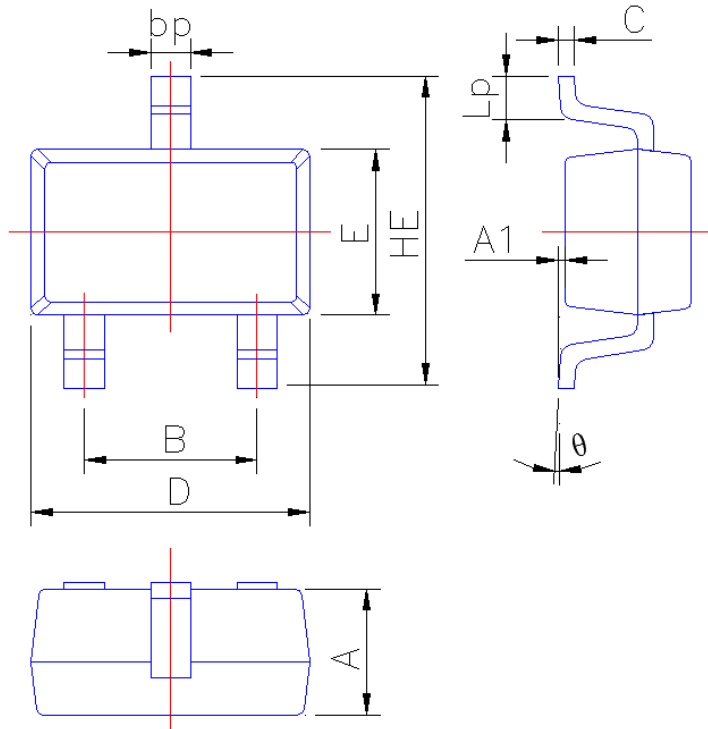


Figure 12. Current-Gain - Bandwidth Product

SOT-323 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°